Paul Fons

List of Publications by Citations

323 papers	9,338 citations	49 h-index	85 g-index
347 ext. papers	10,032 ext. citations	3.5 avg, IF	5.82 L-index

#	Paper	IF	Citations
323	Understanding the phase-change mechanism of rewritable optical media. *Nature Materials*, **2004**, 3, 703-8	27	1057
322	Interfacial phase-change memory. *Nature Nanotechnology*, **2011**, 6, 501-5	28.7	528
321	ZnO transparent conducting films deposited by pulsed laser deposition for solar cell applications. *Thin Solid Films*, **2003**, 431-432, 369-372	2.2	214
320	Toward the ultimate limit of phase change in Ge(2)Sb(2)Te(5). *Nano Letters*, **2010**, 10, 414-9	11.5	201
319	Uniaxial locked epitaxy of ZnO on the a face of sapphire. *Applied Physics Letters*, **2000**, 77, 1801	3.4	178
318	Growth of high-quality epitaxial ZnO films on □Al2O3. *Journal of Crystal Growth*, **1999**, 201-202, 627-632	1.6	162
317	Distortion-triggered loss of long-range order in solids with bonding energy hierarchy. *Nature Chemistry*, **2011**, 3, 311-6	17.6	158
316	Nitrogen-induced defects in ZnO:N grown on sapphire substrate by gas source MBE. *Journal of Crystal Growth*, **2000**, 209, 526-531	1.6	144
315	Raman scattering study of GeTe and Ge2Sb2Te5 phase-change materials. *Journal of Physics and Chemistry of Solids*, **2007**, 68, 1074-1078	3.9	137
314	Ferroelectric Order Control of the Dirac-Semimetal Phase in GeTe-Sb2Te3 Superlattices. *Advanced Materials Interfaces*, **2014**, 1, 1300027	4.6	133
313	Na-induced variations in the structural, optical, and electrical properties of Cu(In,Ga)Se2 thin films. *Journal of Applied Physics*, **2009**, 106, 034908	2.5	126
312	Band-gap modified Al-doped Zn1□MgxO transparent conducting films deposited by pulsed laser deposition. *Applied Physics Letters*, **2004**, 85, 1374-1376	3.4	126
311	Interactions between gallium and nitrogen dopants in ZnO films grown by radical-source molecular-beam epitaxy. *Applied Physics Letters*, **2001**, 79, 4139-4141	3.4	123
310	Direct observation of nitrogen location in molecular beam epitaxy grown nitrogen-doped ZnO. *Physical Review Letters*, **2006**, 96, 045504	7.4	115
309	Band gap energies of bulk, thin-film, and epitaxial layers of CuInSe2 and CuGaSe2. *Journal of Applied Physics*, **1998**, 83, 3678-3689	2.5	107
308	ZnO growth on Si by radical source MBE. *Journal of Crystal Growth*, **2000**, 214-215, 50-54	1.6	106
307	Polarization-induced two-dimensional electron gases in ZnMgO/ZnO heterostructures. *Applied Physics Letters*, **2008**, 93, 202104	3.4	105

306	Two-dimensional electron gas in Zn polar ZnMgO□ZnO heterostructures grown by radical source molecular beam epitaxy. *Applied Physics Letters*, **2006**, 89, 132113	3.4	105
305	Local structure of crystallized GeTe films. *Applied Physics Letters*, **2003**, 82, 382-384	3.4	102
304	Intrinsic complexity of the melt-quenched amorphous Ge2Sb2Te5 memory alloy. *Physical Review B*, **2011**, 83,	3.3	100
303	Pressure-induced site-selective disordering of Ge2Sb2Te5: a new insight into phase-change optical recording. *Physical Review Letters*, **2006**, 97, 035701	7.4	94
302	Fabrication of wide-gap Cu(In1□xGax)Se2 thin film solar cells: a study on the correlation of cell performance with highly resistive i-ZnO layer thickness. *Solar Energy Materials and Solar Cells*, **2005**, 87, 541-548	6.4	91
301	Phase transition in crystalline GeTe: Pitfalls of averaging effects. *Physical Review B*, **2010**, 82,	3.3	83
300	Uniaxial locked growth of high-quality epitaxial ZnO films on -Al2O3. *Journal of Crystal Growth*, **2000**, 209, 532-536	1.6	81
299	Growth of Undoped ZnO Films with Improved Electrical Properties by Radical Source Molecular Beam Epitaxy. *Japanese Journal of Applied Physics*, **2001**, 40, 250-254	1.4	77
298	Photoassisted amorphization of the phase-change memory alloy Ge2Sb2Te5. *Physical Review B*, **2010**, 82,	3.3	69
297	Electrical-field induced giant magnetoresistivity in (non-magnetic) phase change films. *Applied Physics Letters*, **2011**, 99, 152105	3.4	66
296	Giant multiferroic effects in topological GeTe-SbTe superlattices. *Science and Technology of Advanced Materials*, **2015**, 16, 014402	7.1	65
295	Degenerate layers in epitaxial ZnO films grown on sapphire substrates. *Applied Physics Letters*, **2004**, 84, 4412-4414	3.4	63
294	Role of Ge Switch in Phase Transition: Approach using Atomically Controlled GeTe/Sb2Te3Superlattice. *Japanese Journal of Applied Physics*, **2008**, 47, 5763-5766	1.4	62
293	Molecular dynamics simulations of low-energy particle bombardment effects during vapor-phase crystal growth: 10 eV Si atoms incident on Si(001)2□1 surfaces. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **1990**, 8, 3726-3735	2.9	61
292	Vacancy-mediated three-center four-electron bonds in GeTe-Sb2Te3 phase-change memory alloys. *Physical Review B*, **2013**, 87,	3.3	59
291	Determination of crystallographic polarity of ZnO layers. *Applied Physics Letters*, **2005**, 87, 141904	3.4	58
290	Effects of the surface Cu2□Se phase on the growth and properties of CuInSe2 films. *Applied Physics Letters*, **1999**, 74, 1630-1632	3.4	58
289	Alkali incorporation control in Cu(In,Ga)Se2 thin films using silicate thin layers and applications in enhancing flexible solar cell efficiency. *Applied Physics Letters*, **2008**, 93, 124105	3.4	56

288	Heteroepitaxy and characterization of CuInSe2 on GaAs(001). *Journal of Crystal Growth*, **1995**, 150, 1201-1205	1.8	56
287	The order-disorder transition in GeTe: Views from different length-scales. *Applied Physics Letters*, **2011**, 99, 231907	3.4	55
286	Crystallization-induced short-range order changes in amorphous GeTe. *Journal of Physics Condensed Matter*, **2004**, 16, S5103-S5108	1.8	55
285	Structural tuning of wide-gap chalcopyrite CuGaSe2 thin films and highly efficient solar cells: differences from narrow-gap Cu(In,Ga)Se2. *Progress in Photovoltaics: Research and Applications*, **2014**, 22, 821-829	6.8	54
284	Self-organized van der Waals epitaxy of layered chalcogenide structures. *Physica Status Solidi (B): Basic Research*, **2015**, 252, 2151-2158	1.3	54
283	Improved External Efficiency InGaN-Based Light-Emitting Diodes with Transparent Conductive Ga-Doped ZnO as p-Electrodes. *Japanese Journal of Applied Physics*, **2004**, 43, L180-L182	1.4	54
282	Ferroelectric switching in epitaxial GeTe films. *APL Materials*, **2014**, 2, 066101	5.7	53
281	Growth of N-doped and Ga+N-codoped ZnO films by radical source molecular beam epitaxy. *Journal of Crystal Growth*, **2002**, 237-239, 503-508	1.6	53
280	Strong excitonic transition of Zn1−xMgxO alloy. *Applied Physics Letters*, **2007**, 91, 261907	3.4	52
279	Mirror-symmetric magneto-optical Kerr rotation using visible light in [(GeTe)2(Sb2Te3)1]n topological superlattices. *Scientific Reports*, **2014**, 4, 5727	4.9	51
278	Improvement of ZnO TCO film growth for photovoltaic devices by reactive plasma deposition (RPD). *Thin Solid Films*, **2005**, 480-481, 199-203	2.2	50
277	Molecular dynamics and quasidynamics simulations of the annealing of bulk and near-surface interstitials formed in molecular-beam epitaxial Si due to low-energy particle bombardment during deposition. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **1991**, 9, 91-97	2.9	50
276	In situ diagnostic methods for thin-film fabrication: utilization of heat radiation and light scattering. *Progress in Photovoltaics: Research and Applications*, **2004**, 12, 219-234	6.8	49
275	Why Phase-Change Media Are Fast and Stable: A New Approach to an Old Problem. *Japanese Journal of Applied Physics*, **2005**, 44, 3345-3349	1.4	49
274	Atomic Reconfiguration of van der Waals Gaps as the Key to Switching in GeTe/SbTe Superlattices. *ACS Omega*, **2017**, 2, 6223-6232	3.9	48
273	Enhanced crystallization of GeTe from an Sb2Te3 template. *Applied Physics Letters*, **2012**, 100, 021911	3.4	48
272	Changes in electronic structure and chemical bonding upon crystallization of the phase change material GeSb2Te4. *Physical Review Letters*, **2008**, 100, 016402	7.4	48
271	Growth and electrical properties of ZnO thin films deposited by novel ion plating method. *Thin Solid Films*, **2003**, 445, 274-277	2.2	48

270	Excitonic emissions from CuInSe2 on GaAs(001) grown by molecular beam epitaxy. *Applied Physics Letters*, **1995**, 67, 1289-1291	3.4	48
269	Initial structure memory of pressure-induced changes in the phase-change memory alloy Ge2Sb2Te5. *Physical Review Letters*, **2009**, 103, 115502	7.4	47
268	Room-temperature deposition of Al-doped ZnO films by oxygen radical-assisted pulsed laser deposition. *Thin Solid Films*, **2002**, 422, 176-179	2.2	47
267	Femtosecond structural transformation of phase-change materials far from equilibrium monitored by coherent phonons. *Nature Communications*, **2015**, 6, 8367	17.4	46
266	Development of high-efficiency flexible Cu(In,Ga)Se2 solar cells: A study of alkali doping effects on CIS, CIGS, and CGS using alkali-silicate glass thin layers. *Current Applied Physics*, **2010**, 10, S154-S156	2.6	45
265	Local structure of Ge nanoislands on Si(111) surfaces with a SiO2 coverage. *Applied Physics Letters*, **2001**, 78, 2563-2565	3.4	44
264	High quality CuInSe2 films grown on pseudo-lattice-matched substrates by molecular beam epitaxy. *Applied Physics Letters*, **1996**, 69, 647-649	3.4	43
263	Understanding Phase-Change Memory Alloys from a Chemical Perspective. *Scientific Reports*, **2015**, 5, 13698	4.9	41
262	What is the Origin of Activation Energy in Phase-Change Film?. *Japanese Journal of Applied Physics*, **2009**, 48, 03A053	1.4	39
261	Cu(In1−xGax)Se2 growth studies by in situ spectroscopic light scattering. *Applied Physics Letters*, **2003**, 82, 2091-2093	3.4	39
260	Instability and Spontaneous Reconstruction of Few-Monolayer Thick GaN Graphitic Structures. *Nano Letters*, **2016**, 16, 4849-56	11.5	39
259	Measurements of Temperature Dependence of Optical and Thermal Properties of Optical Disk Materials. *Japanese Journal of Applied Physics*, **2006**, 45, 1419-1421	1.4	38
258	Improvement of Electrical Properties in ZnO Thin Films Grown by Radical Source(RS)-MBE. *Physica Status Solidi A*, **2000**, 180, 287-292		38
257	A sensitive multilayered structure suitable for biosensing on the BioDVD platform. *Analytical Chemistry*, **2009**, 81, 4963-70	7.8	37
256	Epitaxial growth of ZnO thin films on LiNbO3 substrates. *Thin Solid Films*, **1999**, 347, 238-240	2.2	37
255	A two-step process for growth of highly oriented Sb2Te3 using sputtering. *AIP Advances*, **2016**, 6, 045220	1.5	37
254	Electronic excitation-induced semiconductor-to-metal transition in monolayer MoTe2. *Physical Review B*, **2016**, 94,	3.3	37
253	On a thermally induced readout mechanism in super-resolution optical disks. *Journal of Applied Physics*, **2006**, 100, 043106	2.5	35

252	Band-edge photoluminescence of CuGaSe2 films grown by molecular beam epitaxy. *Journal of Applied Physics*, **1996**, 79, 4318	2.5	35
251	A shallow state in molecular beam epitaxial grown CuGaSe2 film detectable by 1.62 eV photoluminescence. *Journal of Applied Physics*, **1997**, 81, 2794-2798	2.5	34
250	Measurement of the thermal conductivity of nanometer scale thin films by thermoreflectance phenomenon. *Microelectronic Engineering*, **2007**, 84, 1792-1796	2.5	34
249	Effect of band offset on the open circuit voltage of heterojunction CuIn1−xGaxSe2 solar cells. *Applied Physics Letters*, **2004**, 85, 5607-5609	3.4	34
248	Growth and characterization of undoped ZnO films for single crystal based device use by radical source molecular beam epitaxy (RS-MBE). *Journal of Crystal Growth*, **2001**, 227-228, 923-928	1.6	34
247	Pressure-induced amorphization of quasibinary GeTe–Sb2Te3: The role of vacancies. *Applied Physics Letters*, **2007**, 91, 021911	3.4	33
246	Epitaxy of Ge–Sb–Te phase-change memory alloys. *Applied Physics Letters*, **2009**, 94, 041902	3.4	32
245	Flexible Cu(In,Ga)Se2 solar cells fabricated using alkali-silicate glass thin layers as an alkali source material. *Journal of Renewable and Sustainable Energy*, **2009**, 1, 013102	2.5	32
244	Temperature independence of pressure-induced amorphization of the phase-change memory alloy Ge2Sb2Te5. *Applied Physics Letters*, **2008**, 93, 031918	3.4	32
243	Electrical properties of Si(100) films doped with low-energy (≤150 eV) Sb ions during growth by molecular beam epitaxy. *Applied Physics Letters*, **1988**, 53, 1732-1734	3.4	32
242	Texture and morphology variations in (In,Ga)2Se3 and Cu(In,Ga)Se2 thin films grown with various Se source conditions. *Progress in Photovoltaics: Research and Applications*, **2013**, 21, 544-553	6.8	31
241	High electron mobility Zn polar ZnMgO/ZnO heterostructures grown by molecular beam epitaxy. *Journal of Crystal Growth*, **2007**, 301-302, 358-361	1.6	31
240	Temperature Dependence of the Thermal Properties of Optical Memory Materials. *Japanese Journal of Applied Physics*, **2007**, 46, 3909-3911	1.4	31
239	Bandgap Engineering of ZnO Using Se. *Physica Status Solidi (B): Basic Research*, **2002**, 229, 887-890	1.3	31
238	The effects of thermal treatments on the electrical properties of phosphorus doped ZnO layers grown by MBE. *Journal of Crystal Growth*, **2005**, 278, 268-272	1.6	31
237	Growth of ZnO and device applications. *Applied Surface Science*, **2005**, 244, 504-510	6.7	31
236	Existence of tetrahedral site symmetry about Ge atoms in a single-crystal film of Ge2Sb2Te5 found by x-ray fluorescence holography. *Applied Physics Letters*, **2007**, 90, 131913	3.4	30
235	Epitaxial phase-change materials. *Physica Status Solidi - Rapid Research Letters*, **2012**, 6, 415-417	2.5	29

234	Band profiles of ZnMgO/ZnO heterostructures confirmed by Kelvin probe force microscopy. *Applied Physics Letters*, **2009**, 94, 242107	3.4	29
233	Similarities and Critical Differences in Heavy Alkali-Metal Rubidium and Cesium Effects on Chalcopyrite Cu(In,Ga)Se2 Thin-Film Solar Cells. *Journal of Physical Chemistry C*, **2019**, 123, 17757-17764	3.8	28
232	Ge L3-edge x-ray absorption near-edge structure study of structural changes accompanying conductivity drift in the amorphous phase of Ge2Sb2Te5. *Journal of Applied Physics*, **2014**, 115, 173501	2.5	28
231	Local instability of p-type bonding makes amorphous GeTe a lone-pair semiconductor. *Physical Review B*, **2013**, 87,	3.3	28
230	Selective detection of tetrahedral units in amorphous GeTe-based phase change alloys using Ge L3-edge x-ray absorption near-edge structure spectroscopy. *Applied Physics Letters*, **2013**, 102, 111904	3.4	28
229	Anion vacancies in CuInSe2. *Thin Solid Films*, **2001**, 387, 129-134	2.2	28
228	Origin of resistivity contrast in interfacial phase-change memory: The crucial role of Ge/Sb intermixing. *Applied Physics Letters*, **2019**, 114, 132102	3.4	27
227	Ab-initio calculations and structural studies of (SiTe)2(Sb2Te3)n (n: 1, 2, 4 and 6) phase-change superlattice films. *Physica Status Solidi - Rapid Research Letters*, **2014**, 8, 302-306	2.5	27
226	Non-melting super-resolution near-field apertures in Sb□e alloys. *Applied Physics Letters*, **2010**, 97, 161906	3.4	27
225	Buried p-n junction formation in CuGaSe2 thin-film solar cells. *Applied Physics Letters*, **2014**, 104, 031606	3.4	26
224	Excitation-Assisted Disordering of GeTe and Related Solids with Resonant Bonding. *Journal of Physical Chemistry C*, **2014**, 118, 10248-10253	3.8	25
223	Why DVDs work the way they do: The nanometer-scale mechanism of phase change in Ge□b□e alloys. *Journal of Non-Crystalline Solids*, **2006**, 352, 1612-1615	3.9	25
222	Liquid Ge2Sb2Te5 studied by extended x-ray absorption. *Applied Physics Letters*, **2009**, 95, 241902	3.4	24
221	Growth of polycrystalline Cu(In,Ga)Se2 thin films using a radio frequency-cracked Se-radical beam source and application for photovoltaic devices. *Applied Physics Letters*, **2007**, 91, 041902	3.4	24
220	Crystalline GeTe-based phase-change alloys: Disorder in order. *Physical Review B*, **2012**, 86,	3.3	23
219	Sub-nanometre resolution of atomic motion during electronic excitation in phase-change materials. *Scientific Reports*, **2016**, 6, 20633	4.9	22
218	A Magnetoresistance Induced by a Nonzero Berry Phase in GeTe/Sb2Te3 Chalcogenide Superlattices. *Advanced Functional Materials*, **2017**, 27, 1702243	15.6	22
217	Local structure of nitrogen in N-doped amorphous and crystalline GeTe. *Applied Physics Letters*, **2012**, 100, 061910	3.4	22

216	Direct observation of the Cu2□Se phase of Cu-rich epitaxial CuInSe2 grown on GaAs (001). *Journal of Applied Physics*, **1998**, 84, 6926-6928	2.5	22
215	Doping properties of ZnO thin films for photovoltaic devices grown by URT-IP (ion plating) method. *Thin Solid Films*, **2004**, 451-452, 219-223	2.2	22
214	Characterization of ZnO crystals by photoluminescence spectroscopy. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2004**, 1, 872-875		22
213	Properties of CuInGaSe2 solar cells based upon an improved three-stage process. *Thin Solid Films*, **2003**, 431-432, 6-10	2.2	22
212	Photoluminescence characterization of excitonic centers in ZnO epitaxial films. *Applied Physics Letters*, **2005**, 86, 221907	3.4	22
211	Interfacial alkali diffusion control in chalcopyrite thin-film solar cells. *ACS Applied Materials & Interfaces*, **2014**, 6, 14123-30	9.5	21
210	A hard X-ray nanospectroscopy station at SPring-8 BL39XU. *Journal of Physics: Conference Series*, **2013**, 430, 012017	0.3	21
209	Large grain Cu(In,Ga)Se2 thin film growth using a Se-radical beam source. *Solar Energy Materials and Solar Cells*, **2009**, 93, 792-796	6.4	21
208	Phase-change optical recording: Past, present, future. *Thin Solid Films*, **2007**, 515, 7534-7537	2.2	21
207	Molecular beam epitaxial growth and characterization of CuInSe2 and CuGaSe2 for device applications. *Journal of Crystal Growth*, **2002**, 237-239, 1993-1999	1.6	21
206	Nucleation and growth of ZnO on sapphire substrates using molecular beam epitaxy. *Journal of Crystal Growth*, **2001**, 227-228, 911-916	1.6	21
205	Photoluminescence properties of sodium incorporation in CuInSe2 and CuIn3Se5 thin films. *Solar Energy Materials and Solar Cells*, **2001**, 67, 289-295	6.4	21
204	Reduction in crystallization time of Sb:Te films through addition of Bi. *Applied Physics Letters*, **2008**, 92, 141921	3.4	20
203	An option for the surface science on Cu chalcopyrites: the selenium capping and decapping process. *Surface Science*, **2004**, 557, 263-268	1.8	20
202	An EXAFS and XANES study of MBE grown Cu-doped ZnO. *Nuclear Instruments & Methods in Physics Research B*, **2003**, 199, 190-194	1.2	20
201	Optical characterizations of CuInSe2 epitaxial layers grown by molecular beam epitaxy. *Journal of Applied Physics*, **1999**, 86, 4354-4359	2.5	20
200	Effects of RbF postdeposition treatment and heat-light soaking on the metastable acceptor activation of CuInSe2 thin film photovoltaic devices. *Applied Physics Letters*, **2018**, 113, 063901	3.4	19
199	Local structure of the SnTe topological crystalline insulator: Rhombohedral distortions emerging from the rocksalt phase. *Physical Review B*, **2014**, 90,	3.3	19

198	Effect of doping on global and local order in crystalline GeTe. *Applied Physics Letters*, **2011**, 98, 231907	3.4	19
197	Observation of Exciton-Polariton Emissions from a ZnO Epitaxial Film on the a-Face of Sapphire Grown by Radical-Source Molecular-Beam-Epitaxy. *Japanese Journal of Applied Physics*, **2002**, 41, L935-L937	1.4	19
196	Impact of a binary Ga2Se3 precursor on ternary CuGaSe2 thin-film and solar cell device properties. *Applied Physics Letters*, **2013**, 103, 143903	3.4	18
195	Electronic Structure of Transition-Metal Based Cu2GeTe3 Phase Change Material: Revealing the Key Role of Cu d Electrons. *Chemistry of Materials*, **2017**, 29, 7440-7449	9.6	18
194	Recrystallization of an amorphized epitaxial phase-change alloy: A phoenix arising from the ashes. *Applied Physics Letters*, **2012**, 101, 061903	3.4	18
193	Thermal Conductivity Measurements of SbTe Alloy Thin Films Using a Nanosecond Thermoreflectance Measurement System. *Japanese Journal of Applied Physics*, **2007**, 46, 6863-6864	1.4	18
192	A XANES Study of Cu Valency in Cu-Doped Epitaxial ZnO. *Physica Status Solidi (B): Basic Research*, **2002**, 229, 849-852	1.3	18
191	Ion-beam doping of GaAs with low-energy (100 eV) C+ using combined ion-beam and molecular-beam epitaxy. *Journal of Applied Physics*, **1995**, 77, 146-152	2.5	18
190	The strain energy density of cubic epitaxial layers. *Journal of Crystal Growth*, **1996**, 160, 406-412	1.6	17
189	Growth of CuGaSe2 film by molecular beam epitaxy. *Microelectronics Journal*, **1996**, 27, 53-58	1.8	17
188	Local atomic order of crystalline Ge8Sb2Te11 across the ferroelectric to paraelectric transition: The role of vacancies and static disorder. *Physical Review B*, **2011**, 84,	3.3	16
187	In situ deposition rate monitoring during the three-stage-growth process of Cu(In,Ga)Se2 absorber films. *Thin Solid Films*, **2003**, 431-432, 16-21	2.2	16
186	Static analysis of off-axis crystal film growth onto a lattice-mismatched substrate. *Applied Physics Letters*, **2001**, 79, 608-610	3.4	16
185	Low energy (100 eV) C+ ion doping into GaAs using combined ion beam and molecular beam epitaxial technology. *Applied Physics Letters*, **1993**, 63, 1951-1953	3.4	16
184	High-quality sputter-grown layered chalcogenide films for phase change memory applications and beyond. *Journal Physics D: Applied Physics*, **2020**, 53, 284002	3	15
183	Manipulating the Bulk Band Structure of Artificially Constructed van der Waals Chalcogenide Heterostructures. *ACS Applied Materials & Interfaces*, **2017**, 9, 23918-23925	9.5	15
182	Polarization dependent optical control of atomic arrangement in multilayer Ge-Sb-Te phase change materials. *Applied Physics Letters*, **2012**, 101, 232101	3.4	15
181	Characteristics of nanostructured Ag films by the reduction of sputtered AgOxthin films. *Nanotechnology*, **2006**, 17, 79-82	3.4	15

180	A possible mechanism of ultrafast amorphization in phase-change memory alloys: an ion slingshot from the crystalline to amorphous position. *Journal of Physics Condensed Matter*, **2007**, 19, 455209	1.8	15
179	Soft X-ray XANES of N in ZnO:N □Why is doping so difficult?. *Nuclear Instruments & Methods in Physics Research B*, **2006**, 246, 75-78	1.2	15
178	Strain engineering of atomic and electronic structures of few-monolayer-thick GaN. *Physical Review Materials*, **2017**, 1,	3.2	15
177	Compositional tuning in sputter-grown highly-oriented Bi-Te films and their optical and electronic structures. *Nanoscale*, **2017**, 9, 15115-15121	7.7	14
176	Coherent phonon study of (GeTe)l(Sb2Te3)m interfacial phase change memory materials. *Applied Physics Letters*, **2014**, 105, 151902	3.4	14
175	A reconsideration of the thermodynamics of phase-change switching. *Physica Status Solidi (B): Basic Research*, **2012**, 249, 1932-1938	1.3	14
174	Effects of annealing on CuInSe2 films grown by molecular beam epitaxy. *Solar Energy Materials and Solar Cells*, **1997**, 49, 319-326	6.4	14
173	Growth of LiNbO3 epitaxial films by oxygen radical-assisted laser molecular beam epitaxy. *Applied Physics A: Materials Science and Processing*, **1999**, 69, S679-S681	2.6	14
172	Cr-Triggered Local Structural Change in CrGeTe Phase Change Material. *ACS Applied Materials & Interfaces*, **2019**, 11, 43320-43329	9.5	13
171	Picosecond strain dynamics in Ge2Sb2Te5 monitored by time-resolved x-ray diffraction. *Physical Review B*, **2014**, 90,	3.3	13
170	Pressure-induced structural transitions in phase-change materials based on Ge-free Sb-Te alloys. *Physical Review B*, **2011**, 83,	3.3	13
169	Observation of diamond crystallites in thin films prepared by laser ablation of hard fullerene-based carbon. *Journal Physics D: Applied Physics*, **1996**, 29, 929-933	3	13
168	Epitaxial growth of Si by ArF laser-excited supersonic free jets of Si2H6. *Applied Physics Letters*, **1993**, 63, 3473-3475	3.4	13
167	Zener Tunneling Breakdown in Phase-Change Materials Revealed by Intense Terahertz Pulses. *Physical Review Letters*, **2018**, 121, 165702	7.4	13
166	Terahertz spectroscopic characterization of Ge2Sb2Te5 phase change materials for photonics applications. *Journal of Materials Chemistry C*, **2019**, 7, 8209-8215	7.1	12
165	High-Speed Bipolar Switching of Sputtered Ge□e/Sb□e Superlattice iPCM with Enhanced Cyclability. *Physica Status Solidi - Rapid Research Letters*, **2019**, 13, 1900105	2.5	12
164	Local structure of the crystalline and amorphous states of Ga2Te3 phase-change alloy without resonant bonding: A combined x-ray absorption and ab initio study. *Physical Review B*, **2017**, 95,	3.3	12
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162	Local structure of amorphous Ge?Sb?Te alloys: Ge umbrella flip vs. DFT simulations. *Physica Status Solidi (B): Basic Research*, **2009**, 246, 1826-1830	1.3	12
161	Sub-Nanosecond Time-Resolved Structural Measurements of the Phase-Change Alloy Ge2Sb2Te5. *Japanese Journal of Applied Physics*, **2007**, 46, 3711-3714	1.4	12
160	Si-Doping Effects in Cu(In,Ga)Se Thin Films and Applications for Simplified Structure High-Efficiency Solar Cells. *ACS Applied Materials & Interfaces*, **2017**, 9, 31119-31128	9.5	11
159	Athermal amorphization of crystallized chalcogenide glasses and phase-change alloys. *Physica Status Solidi (B): Basic Research*, **2014**, 251, 1297-1308	1.3	11
158	CIGS thin films, solar cells, and submodules fabricated using a rf-plasma cracked Se-radical beam source. *Thin Solid Films*, **2011**, 519, 7216-7220	2.2	11
157	Temperature dependence of photoacoustic spectra in CuInSe2 thin films grown by molecular beam epitaxy. *Solar Energy Materials and Solar Cells*, **1998**, 50, 127-132	6.4	11
156	InGaN-based light-emitting diodes fabricated with transparent Ga-doped ZnO as ohmic p-contact. *Physica Status Solidi A*, **2004**, 201, 2704-2707		11
155	Adjusting the sodium diffusion into CuInGaSe2 absorbers by preheating of Mo/SLG substrates. *Journal of Physics and Chemistry of Solids*, **2003**, 64, 1877-1880	3.9	11
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153	Enhanced Sb2S3 crystallisation by electric field induced silver doping. *Thin Solid Films*, **2016**, 616, 80-85	2.2	11
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